# CY54/74FCT157T

SCCS014 - May 1994 - Revised February 2000

# **Quad 2-Input Multiplexer**

#### **Features**

- Function, pinout, and drive compatible with FCT and F logic
- FCT-C speed at 4.3 ns max. (Com'l), FCT-A speed at 5.0 ns max. (Com'l)
- Reduced V<sub>OH</sub> (typically = 3.3V) versions of equivalent FCT functions
- Edge-rate control circuitry for significantly improved noise characteristics
- · Power-off disable feature
- · Matched rise and fall times
- Fully compatible with TTL input and output logic levels
- ESD > 2000V
- Extended commercial range of -40°C to +85°C

• Sink current 64 mA (Com'l),

32 mA (Mil)
Source current 32 mA (Com'l),

12 mA (Mil)

### **Functional Description**

The FCT157T is a quad two-input multiplexer that selects four bits of data from two sources under the control of a common data Select input (S). The Enable input ( $\overline{E}$ ) is Active LOW. When ( $\overline{E}$ ) is HIGH, all of the outputs (Y) are forced LOW regardless of all other input conditions.

Moving data from two groups of registers to four common output buses is a common use of the FCT157T. The state of the Select input determines the particular register from which the data comes. It can also be used as a function generator. The device is useful for implementing highly irregular logic by generating any four of the sixteen different functions of two variables with one variable common.

The FCT157T is a logic implementation of a four-pole, two-position switch where the position of the switch is determined by the logic levels supplied to the Select input.

The outputs are designed with a power-off disable feature to allow for live insertion of boards.

#### Logic Block Diagram, FCT157T **Pin Configurations** $l_{1a}$ loh $I_{1b}$ $I_{1c}$ LCC SOIC/QSOP **Top View Top View** <sup>무</sup> 윤 우 <sup>무</sup> 프 S 16**□** V<sub>CC</sub> 6 5 4 15 ☐ E I<sub>0a</sub> Yh $I_{0d}$ I<sub>1a</sub> **□** 3 **GND** 10 S Ya ☐4 FCT157T NC FCT157T 13 l<sub>1d</sub> Y<sub>C</sub> 12 Yd $I_{1c}$ □ I<sub>0c</sub> $I_{1b}$ 1516 17 18 10 🔲 I<sub>1c</sub> Yb GND [ <u>2</u> 2 2 5 Logic Symbol Ē $I_{0d}$ S FCT157T FCT157T-1



# **Pin Description**

Name	Description				
S Common Select Input					
E Enable Inputs (Active LOW)					
I <sub>0</sub> Data Inputs from Source 0					
I <sub>1</sub> Data Inputs from Source 1					
Υ	Non-Inverted Output				

### Function Table<sup>[1]</sup>

	Inp	Outputs		
E	S	I <sub>0</sub>	I <sub>1</sub>	Y
Н	Х	Х	Х	L
L	Н	Х	L	L
L	Н	Х	Н	Н
L	L	L	Х	L
L	L	Н	Х	Н

# Maximum Ratings<sup>[2,3]</sup>

(Above which the useful life may be impaired. For user guilines, not tested.)	ide-
Storage Temperature65°C to +150	)°C
Ambient Temperature with	
Power Applied–65°C to +135	°C
Supply Voltage to Ground Potential0.5V to +7.	0V
DC Input Voltage0.5V to +7.	0V
DC Output Voltage0.5V to +7.	0V
DC Output Current (Maximum Sink Current/Pin) 120 r	nΑ
Power Dissipation	5W
Static Discharge Voltage>200 (per MIL-STD-883, Method 3015)	1V

### **Operating Range**

Range	Range	Ambient Temperature	v <sub>cc</sub>
Commercial	All	–40°C to +85°C	5V ± 5%
Military <sup>[4]</sup>	All	–55°C to +125°C	5V ± 10%

### **Electrical Characteristics** Over the Operating Range

Parameter	Description	Test Condition	Min.	<b>Typ</b> . <sup>[5]</sup>	Max.	Unit	
V <sub>OH</sub>	Output HIGH Voltage	V <sub>CC</sub> =Min., I <sub>OH</sub> =-32 mA	Com'l	2.0			V
		V <sub>CC</sub> =Min., I <sub>OH</sub> =-15 mA	Com'l	2.4	3.3		V
		V <sub>CC</sub> =Min., I <sub>OH</sub> =-12 mA	Mil	2.4	3.3		V
V <sub>OL</sub>	Output LOW Voltage	V <sub>CC</sub> =Min., I <sub>OL</sub> =64 mA	Com'l		0.3	0.55	V
		V <sub>CC</sub> =Min., I <sub>OL</sub> =32 mA	Mil		0.3	0.55	V
V <sub>IH</sub>	Input HIGH Voltage			2.0			V
V <sub>IL</sub>	Input LOW Voltage					0.8	V
V <sub>H</sub>	Hysteresis <sup>[6]</sup>	All inputs			0.2		V
V <sub>IK</sub>	Input Clamp Diode Voltage	V <sub>CC</sub> =Min., I <sub>IN</sub> =-18 mA			-0.7	-1.2	V
I <sub>I</sub>	Input HIGH Current	V <sub>CC</sub> =Max., V <sub>IN</sub> =V <sub>CC</sub>				5	μΑ
I <sub>IH</sub>	Input HIGH Current	V <sub>CC</sub> =Max., V <sub>IN</sub> =2.7V				±1	μΑ
I <sub>IL</sub>	Input LOW Current	V <sub>CC</sub> =Max., V <sub>IN</sub> =0.5V				±1	μΑ
I <sub>OZH</sub>	Off State HIGH-Level Output Current	$V_{CC} = Max., V_{OUT} = 2.7V$				10	μА
I <sub>OZL</sub>	Off State LOW-Level Output Current	$V_{CC} = Max., V_{OUT} = 0.5V$				-10	μА
I <sub>OS</sub>	Output Short Circuit Current <sup>[7]</sup>	V <sub>CC</sub> =Max., V <sub>OUT</sub> =0.0V		-60	-120	-225	mA
I <sub>OFF</sub>	Power-Off Disable	V <sub>CC</sub> =0V, V <sub>OUT</sub> =4.5V				±1	μΑ

#### Note:

- H = HIGH Voltage Level. L = LOW Voltage Level. X = Don't Care
  Unless otherwise noted, these limits are over the operating free-air temperature range.
  Unused inputs must always be connected to an appropriate logic voltage level, preferably either V<sub>CC</sub> or ground.
  T<sub>A</sub> is the "instant on" case temperature.
  Typical values are at V<sub>CC</sub>=5.0V, T<sub>A</sub>=+25°C ambient.
  This parameter is specified but not tested.

- Not more than one output should be shorted at a time. Duration of short should not exceed one second. The use of high-speed test apparatus and/or sample and hold techniques are preferable in order to minimize internal chip heating and more accurately reflect operational values. Otherwise prolonged shorting of a high output may raise the chip temperature well above normal and thereby cause invalid readings in other parametric tests. In any sequence of parameter tests, I<sub>OS</sub> tests should be performed last.



# Capacitance<sup>[6]</sup>

Parameter	Description	Typ. <sup>[5]</sup>	Max.	Unit
C <sub>IN</sub>	Input Capacitance	5	10	pF
C <sub>OUT</sub>	Output Capacitance	9	12	pF

# **Power Supply Characteristics**

Parameter	Description	Test Conditions	<b>Typ.</b> <sup>[5]</sup>	Max.	Unit
I <sub>CC</sub>	Quiescent Power Supply Current	V <sub>CC</sub> =Max., V <sub>IN</sub> ≤0.2V, V <sub>IN</sub> ≥V <sub>CC</sub> -0.2V	0.1	0.2	mA
Δl <sub>CC</sub>	Quiescent Power Supply Current (TTL inputs HIGH)	V <sub>CC</sub> =Max., V <sub>IN</sub> =3.4V, <sup>[8]</sup> f <sub>1</sub> =0, Outputs Open	0.5	2.0	mA
I <sub>CCD</sub>	Dynamic Power Supply Current <sup>[9]</sup>	V <sub>CC</sub> =Max., One Input Toggling, 50% Duty Cycle, Outputs Open, OE=GND, V <sub>IN</sub> ≤0.2V or V <sub>IN</sub> ≥V <sub>CC</sub> -0.2V	0.06	0.12	mA/MHz
I <sub>C</sub>	Total Power Supply Current <sup>[10]</sup>	V <sub>CC</sub> =Max., 50% Duty Cycle, Outputs Open, One Input Toggling at f <sub>1</sub> =10 MHz, OE=GND, V <sub>IN</sub> ≤0.2V or V <sub>IN</sub> ≥V <sub>CC</sub> -0.2V	0.7	1.4	mA
		V <sub>CC</sub> =Max., 50% Duty Cycle, Outputs Open, One Input Toggling at f <sub>1</sub> =10 MHz, OE=GND, V <sub>IN</sub> =3.4V or V <sub>IN</sub> =GND	1.0	2.4	mA
		V <sub>CC</sub> =Max., 50% Duty Cycle, Outputs Open, Four Bits Toggling at f <sub>1</sub> =2.5 MHz, OE=GND, V <sub>IN</sub> ≤0.2V or V <sub>IN</sub> ≥V <sub>CC</sub> -0.2V	0.7	1.4 <sup>[11]</sup>	mA
		V <sub>CC</sub> =Max., 50% Duty Cycle, Outputs Open, Four Bits Toggling at f <sub>1</sub> =2.5 MHz, OE=GND, V <sub>IN</sub> =3.4V or V <sub>IN</sub> =GND	1.7	5.4 <sup>[11]</sup>	mA

#### Notes:

Notes:

8. Per TTL driven input (V<sub>IN</sub>=3.4V); all other inputs at V<sub>CC</sub> or GND.

9. This parameter is not directly testable, but is derived for use in Total Power Supply calculations.

10. I<sub>C</sub> = I<sub>QUIESCENT</sub> + I<sub>INPUTS</sub> + I<sub>DYNAMIC</sub>
I<sub>C</sub> = I<sub>CC</sub>+ΔI<sub>CC</sub>D<sub>H</sub>N<sub>T</sub>+I<sub>CC</sub>D(f<sub>0</sub>/2 + f<sub>1</sub>N<sub>1</sub>)
I<sub>CC</sub> = Quiescent Current with CMOS input levels

ΔI<sub>CC</sub> = Power Supply Current for a TTL HIGH input (V<sub>IN</sub>=3.4V)
D<sub>H</sub> = Duty Cycle for TTL inputs HIGH
N<sub>T</sub> = Number of TTL inputs at D<sub>H</sub>
I<sub>CCD</sub> = Dynamic Current caused by an input transition pair (HLH or LHL)
f<sub>0</sub> = Clock frequency for registered devices, otherwise zero

= Clock frequency for registered devices, otherwise zero

= Input signal frequency

N<sub>1</sub> = Number of inputs changing at f<sub>1</sub>
All currents are in milliamps and all frequencies are in megahertz.

11. Values for these conditions are examples of the I<sub>CC</sub> formula. These limits are specified but not tested.



# Switching Characteristics Over the Operating Range

			FCT157T FCT157AT			FCT157CT					
			ercial	Milit	ary	ry Commercial		Commercial			Fig
Parameter	Description	Min. <sup>[12]</sup>	Max.	Min. <sup>[12]</sup>	Max.	Min. <sup>[12]</sup>	Max.	Min. <sup>[12]</sup>	Max.	Unit	Fig. No. <sup>[13</sup>
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay I to Y	1.5	6.0	1.5	5.8	1.5	5.0	1.5	4.3	ns	1, 3
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay E to Y	1.5	10.5	1.5	7.4	1.5	6.0	1.5	4.8	ns	1, 5
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay S to Y	1.5	10.5	1.5	8.1	1.5	7.0	1.5	5.2	ns	1, 3

# **Ordering Information**

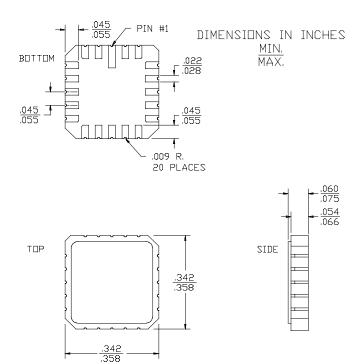
Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
4.3	CY74FCT157CTQCT	Q1	16-Lead (150-Mil) QSOP	Commercial
	CY74FCT157CTSOC/SOCT	S1	16-Lead (300-Mil) Molded SOIC	
5.0	CY74FCT157ATQCT	Q1	16-Lead (150-Mil) QSOP	Commercial
	CY74FCT157ATSOC/SOCT	S1	16-Lead (300-Mil) Molded SOIC	
5.8	CY54FCT157ATLMB	L61	20-Pin Square Leadless Chip Carrier	Military

#### Note:

- 12. Minimum limits are specified but not tested on Propagation Delays.
  13. See "Parameter Measurement Information" in the General Information Section

Document #: 38-00288-C **Package Diagrams** 

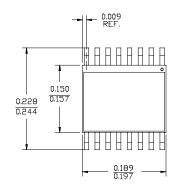
### 20-Pin Square Leadless Chip Carrier L61 MIL-STD-1835 C-2A

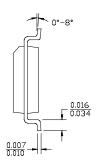


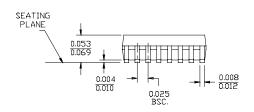


## Package Diagrams (continued)

### 16-Lead Quarter Size Outline Q1

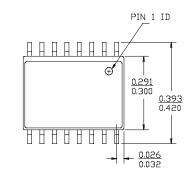




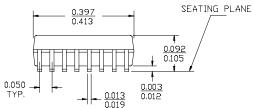


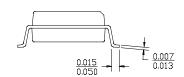
DIMENSIONS IN INCHES  $\frac{\text{MIN.}}{\text{MAX.}}$  LEAD COPLANARITY 0.004 MAX.

### 16-Lead Molded SOIC S1



DIMENSIONS IN INCHES  $\frac{\text{MIN.}}{\text{MAX.}}$  LEAD COPLANARITY 0.004 MAX.





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